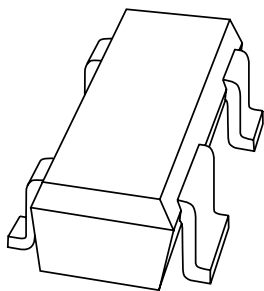


DATA SHEET



BFG590W; BFG590W/X NPN 5 GHz wideband transistors

Product specification
Supersedes data of August 1995

1998 Oct 15

NPN 5 GHz wideband transistors

BFG590W; BFG590W/X

FEATURES

- High power gain
- Low noise figure
- High transition frequency
- Gold metallization ensures excellent reliability.

APPLICATIONS

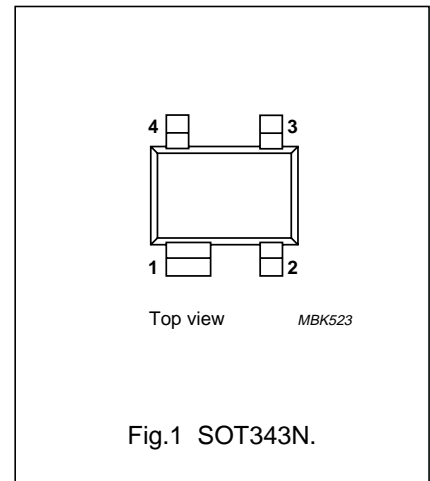
- MATV/CATV amplifiers and RF communications subscriber equipment in the GHz range
- Ideally suitable for use in class-A, (A)B and C amplifiers with either pulsed or continuous drive.

DESCRIPTION

NPN silicon planar epitaxial transistor in a 4-pin dual-emitter SOT343N plastic package.

PINNING

PIN	DESCRIPTION
BFG590W	
1	collector
2	base
3	emitter
4	emitter
BFG590W/X	
1	collector
2	emitter
3	base
4	emitter



MARKING

TYPE NUMBER	CODE
BFG590W	T1
BFG590W/X	T2

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–	20	V
V_{CEO}	collector-emitter voltage	open base	–	–	15	V
I_C	collector current (DC)		–	–	200	mA
P_{tot}	total power dissipation	$T_s \leq 85\text{ }^\circ\text{C}$	–	–	500	mW
h_{FE}	DC current gain	$I_C = 70\text{ mA}; V_{CE} = 8\text{ V}$	60	90	250	
C_{re}	feedback capacitance	$I_C = 0; V_{CB} = 8\text{ V}; f = 1\text{ MHz}$	–	0.7	–	pF
f_T	transition frequency	$I_C = 80\text{ mA}; V_{CE} = 4\text{ V}; f = 1\text{ GHz}; T_{amb} = 25\text{ }^\circ\text{C}$	–	5	–	GHz
G_{UM}	maximum unilateral power gain	$I_C = 80\text{ mA}; V_{CE} = 4\text{ V}; f = 900\text{ MHz}; T_{amb} = 25\text{ }^\circ\text{C}$	–	13	–	dB
$ S_{21} ^2$	insertion power gain	$I_C = 80\text{ mA}; V_{CE} = 4\text{ V}; f = 900\text{ MHz}; T_{amb} = 25\text{ }^\circ\text{C}$	–	11	–	dB

NPN 5 GHz wideband transistors

BFG590W; BFG590W/X

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	20	V
V_{CEO}	collector-emitter voltage	open base	–	15	V
V_{EBO}	emitter-base voltage	open collector	–	3	V
I_C	collector current (DC)		–	200	mA
P_{tot}	total power dissipation	$T_s \leq 85\text{ °C}$; see Fig.2; note 1	–	500	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	175	°C

Note

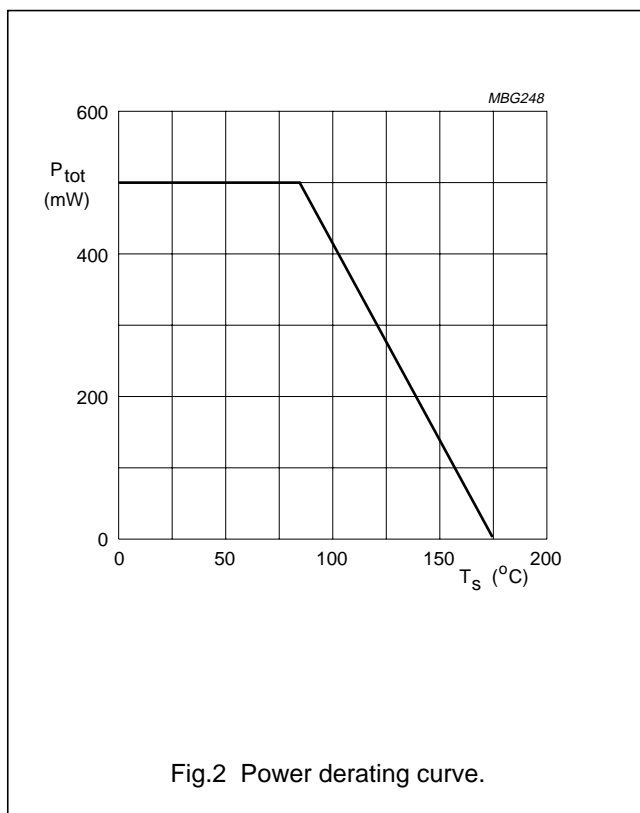
- T_s is the temperature at the soldering point of the collector pin.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-s}$	thermal resistance from junction to soldering point	$T_s \leq 85\text{ °C}$; note 1	180	K/W

Note

- T_s is the temperature at the soldering point of the collector pin.



NPN 5 GHz wideband transistors

BFG590W; BFG590W/X

CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

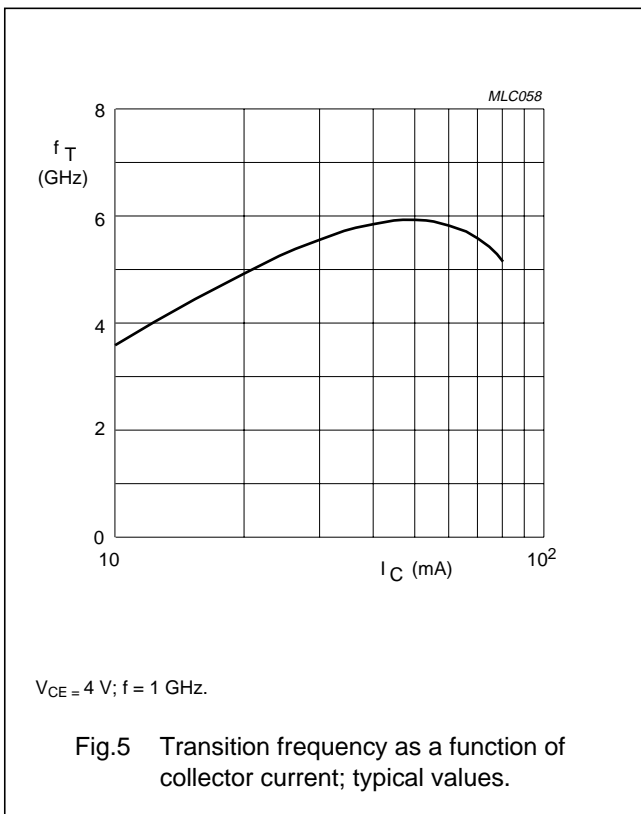
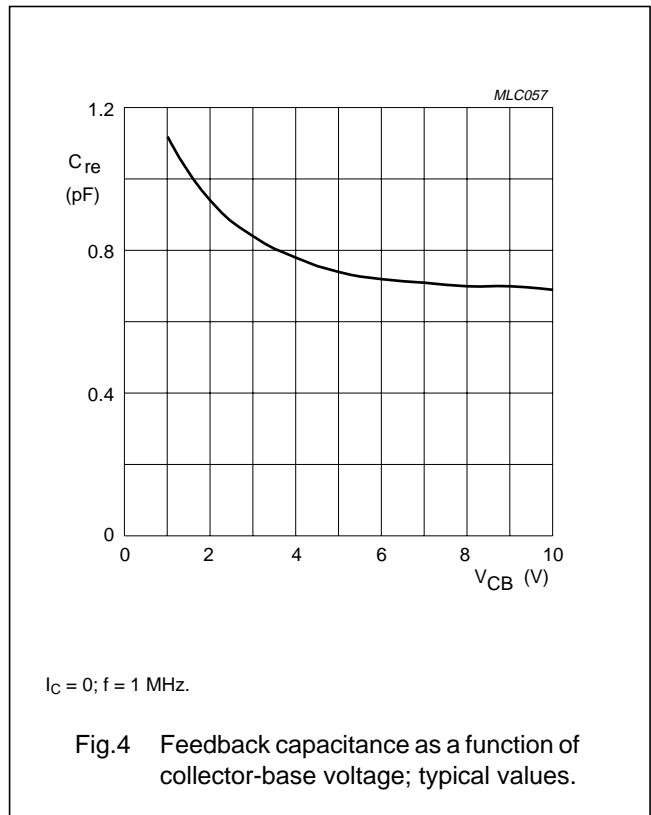
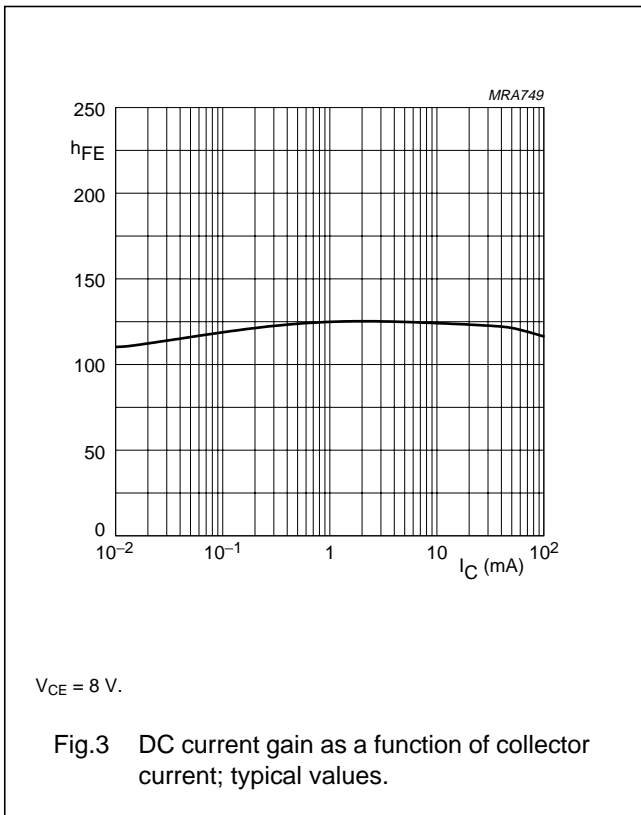
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = 0.1\text{ mA}; I_E = 0$	20	–	–	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = 10\text{ mA}; I_B = 0$	15	–	–	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	$I_E = 0.1\text{ mA}; I_C = 0$	3	–	–	V
I_{CBO}	collector leakage current	$V_{CB} = 10\text{ V}; I_E = 0$	–	–	100	nA
h_{FE}	DC current gain	$I_C = 70\text{ mA}; V_{CE} = 8\text{ V}$	60	90	250	
f_T	transition frequency	$I_C = 80\text{ mA}; V_{CE} = 4\text{ V}; f = 1\text{ GHz}; T_{amb} = 25\text{ °C}$	–	5	–	GHz
C_{re}	feedback capacitance	$I_C = 0; V_{CB} = 8\text{ V}; f = 1\text{ MHz}$	–	0.7	–	pF
G_{UM}	maximum unilateral power gain; note 1	$I_C = 80\text{ mA}; V_{CE} = 4\text{ V}; f = 900\text{ MHz}; T_{amb} = 25\text{ °C}$	–	13	–	dB
		$I_C = 80\text{ mA}; V_{CE} = 4\text{ V}; f = 2\text{ GHz}; T_{amb} = 25\text{ °C}$	–	7.5	–	dB
$ S_{21} ^2$	insertion power gain	$I_C = 80\text{ mA}; V_{CE} = 4\text{ V}; f = 1\text{ GHz}; T_{amb} = 25\text{ °C}$	–	11	–	dB
P_{L1}	output power at 1 dB gain compression	$I_C = 80\text{ mA}; V_{CE} = 5\text{ V}; f = 900\text{ MHz}; R_L = 50\text{ }\Omega; T_{amb} = 25\text{ °C}$	–	21	–	dBm

Note

1. G_{UM} is the maximum unilateral power gain, assuming S_{12} is zero. $G_{UM} = 10 \log \frac{|S_{21}|^2}{(1 - |S_{11}|^2)(1 - |S_{22}|^2)}$ dB.

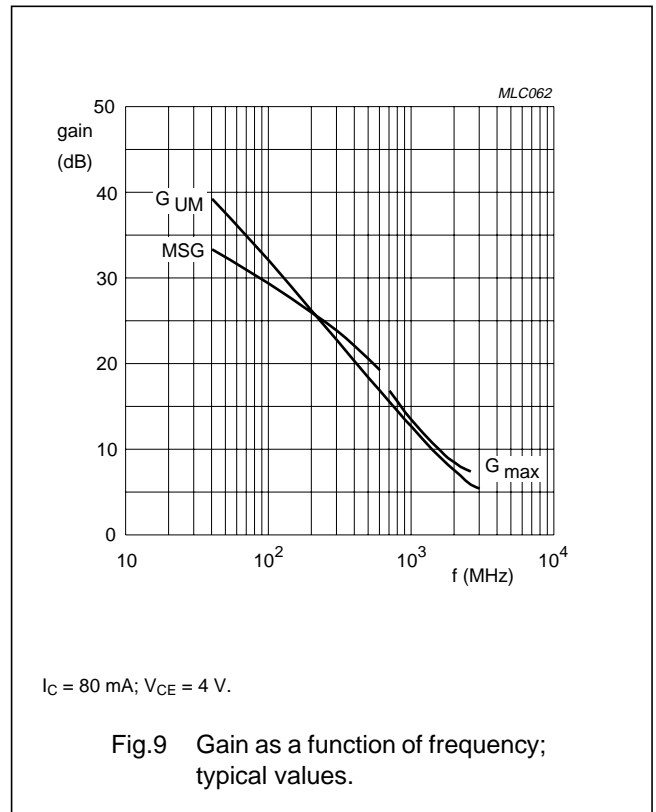
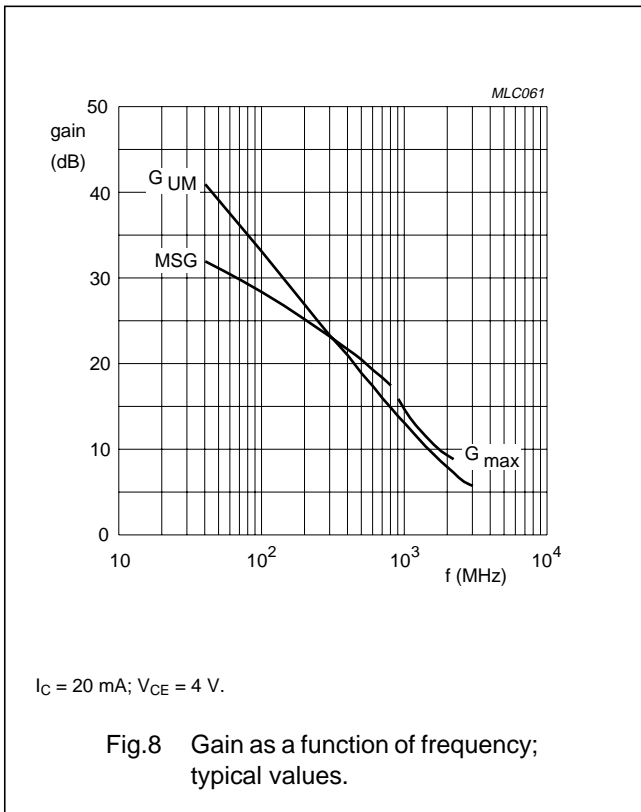
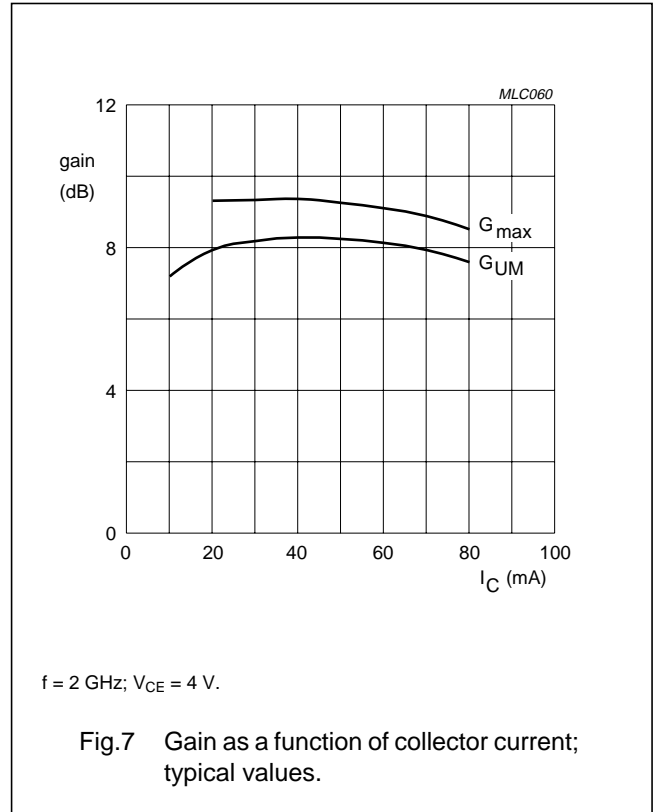
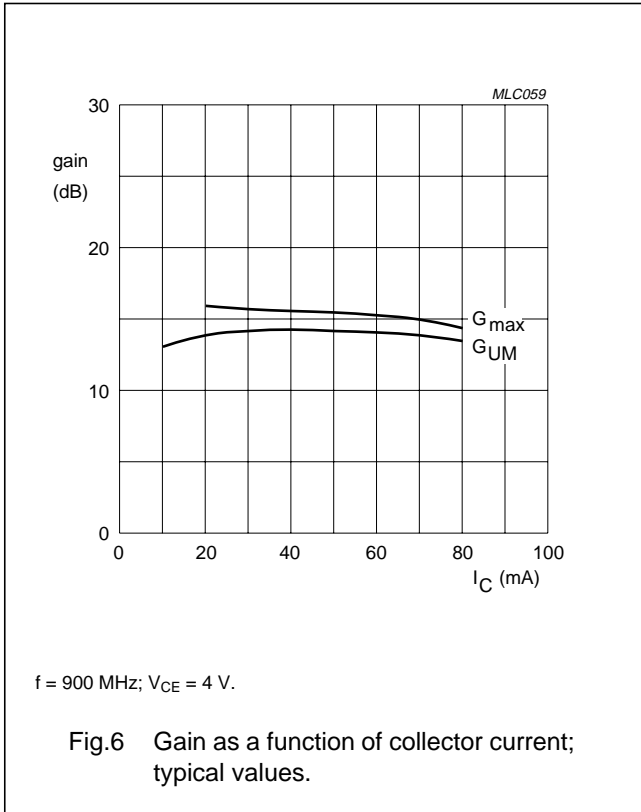
NPN 5 GHz wideband transistors

BFG590W; BFG590W/X



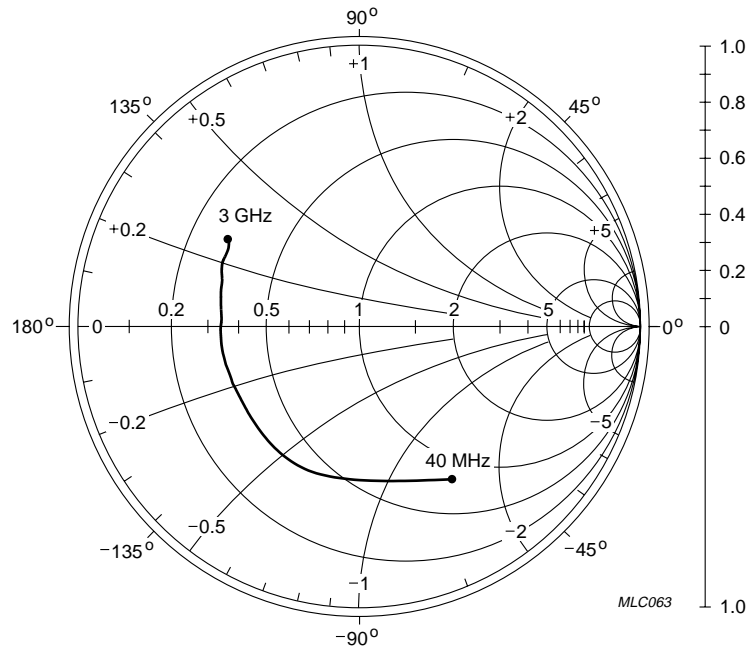
NPN 5 GHz wideband transistors

BFG590W; BFG590W/X



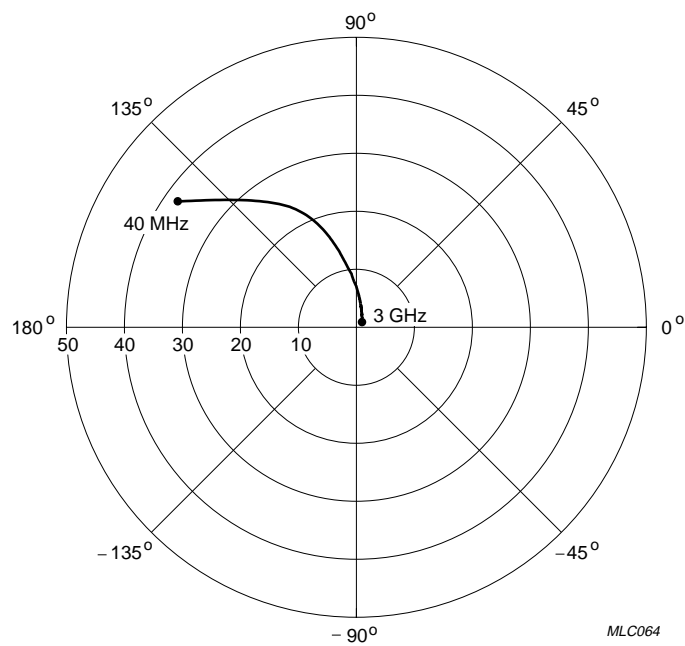
NPN 5 GHz wideband transistors

BFG590W; BFG590W/X



$I_C = 80 \text{ mA}$; $V_{CE} = 4 \text{ V}$; $Z_0 = 50 \Omega$.

Fig.10 Common emitter input reflection coefficient (S_{11}); typical values.

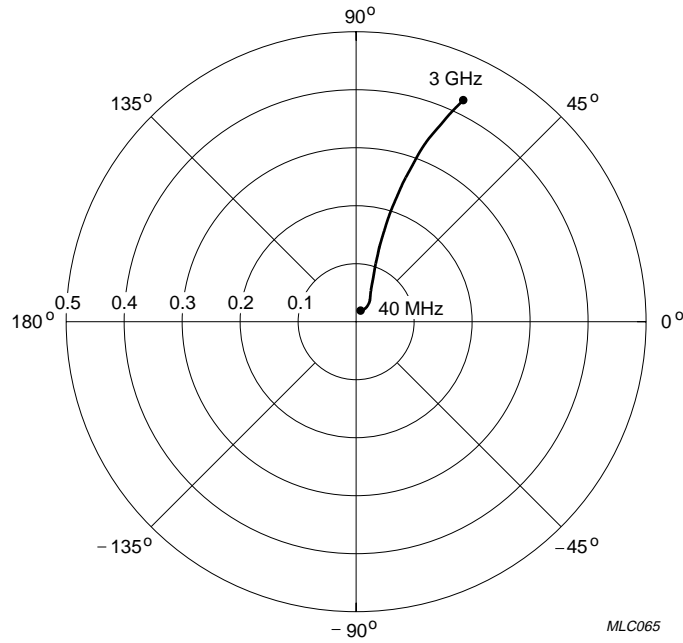


$I_C = 80 \text{ mA}$; $V_{CE} = 4 \text{ V}$.

Fig.11 Common emitter forward transmission coefficient (S_{21}); typical values.

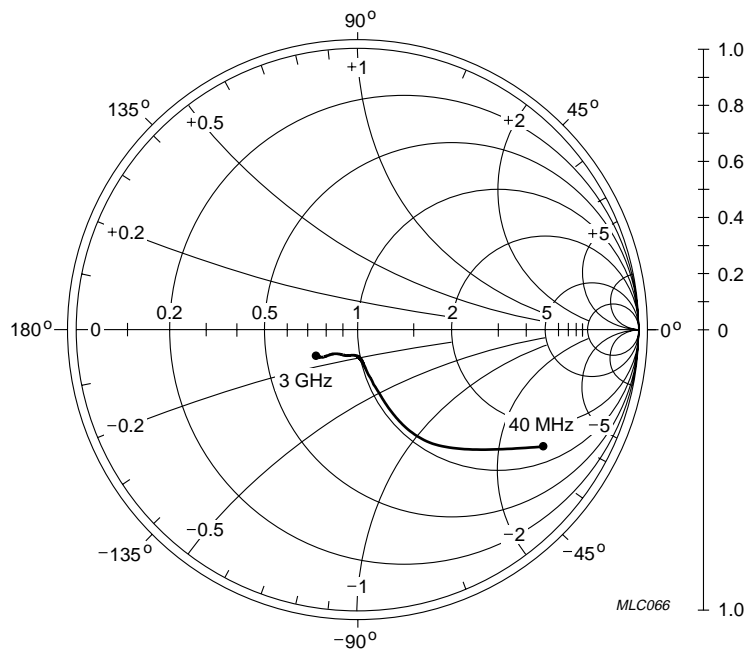
NPN 5 GHz wideband transistors

BFG590W; BFG590W/X



$I_C = 80 \text{ mA}; V_{CE} = 4 \text{ V}.$

Fig.12 Common emitter reverse transmission coefficient (S_{12}); typical values.



$I_C = 80 \text{ mA}; V_{CE} = 4 \text{ V}; Z_0 = 50 \Omega.$

Fig.13 Common emitter output reflection coefficient (S_{22}); typical values.

NPN 5 GHz wideband transistors

BFG590W; BFG590W/X

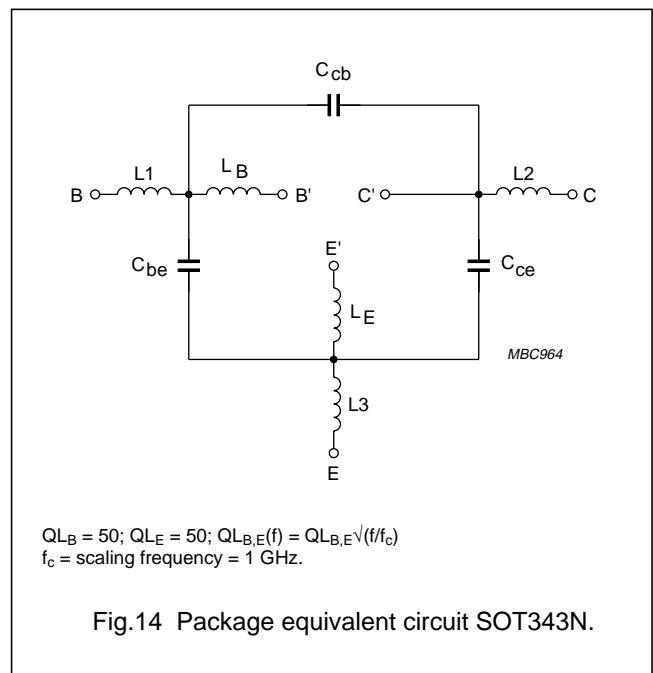
SPICE parameters for the BFG590W die

SEQUENCE No.	PARAMETER	VALUE	UNIT
1	IS	1.341	fA
2	BF	123.5	–
3	NF	0.988	–
4	VAF	75.85	V
5	IKF	9.656	A
6	ISE	232.2	fA
7	NE	2.134	–
8	BR	10.22	–
9	NR	1.016	–
10	VAR	1.992	V
11	IKR	294.1	mA
12	ISC	211.0	aA
13	NC	0.997	–
14	RB	5.000	Ω
15	IRB	1.000	μA
16	RBM	5.000	Ω
17	RE	1.275	Ω
18	RC	920.6	mΩ
19 (1)	XTB	0.000	–
20 (1)	EG	1.110	eV
21 (1)	XTI	3.000	–
22	CJE	3.821	pF
23	VJE	600.0	mV
24	MJE	0.348	–
25	TF	13.60	ps
26	XTF	71.73	–
27	VTF	10.28	V
28	ITF	1.929	A
29	PTF	0.000	deg
30	CJC	1.409	pF
31	VJC	219.4	mV
32	MJC	0.166	–
33	XCJC	0.150	–
34	TR	2.340	ns
35 (1)	CJS	0.000	F

SEQUENCE No.	PARAMETER	VALUE	UNIT
36 (1)	VJS	750.0	mV
37 (1)	MJS	0.000	–
38	FC	0.733	–

Note

1. These parameters have not been extracted, the default values are shown.



List of components (see Fig.14)

DESIGNATION	VALUE	UNIT
C _{be}	70	fF
C _{cb}	50	fF
C _{ce}	115	fF
L1	0.34	nH
L2	0.10	nH
L3	0.25	nH
L _B	0.40	nH
L _E	0.40	nH

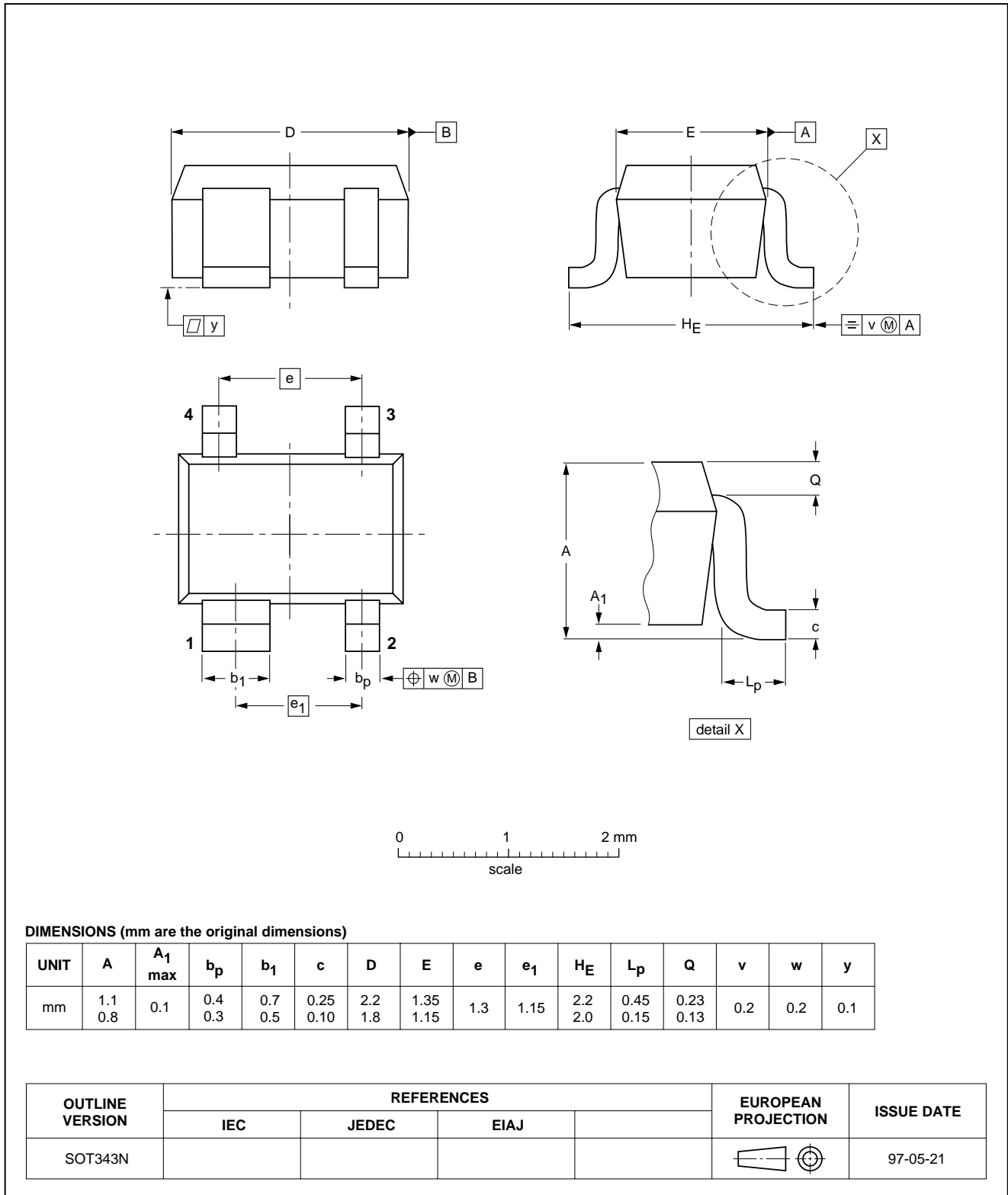
NPN 5 GHz wideband transistors

BFG590W; BFG590W/X

PACKAGE OUTLINE

Plastic surface mounted package; 4 leads

SOT343N



NPN 5 GHz wideband transistors

BFG590W; BFG590W/X

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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